

## N-Channel Super Junction Power MOSFET IV

### General Description

The series of devices use advanced trench gate super junction technology and design to provide excellent  $R_{DS(ON)}$  with low gate charge. This super junction MOSFET fits the industry's AC-DC SMPS requirements for PFC, AC/DC power conversion, and industrial power applications.

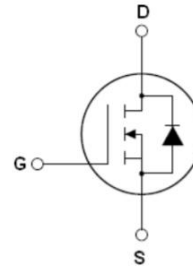
### Features

- New technology for high voltage device
- Low on-resistance and low conduction losses
- Small package
- Ultra Low Gate Charge cause lower driving requirements
- 100% Avalanche Tested
- ROHS compliant

### Application

- Power factor correction (PFC)
- Switched mode power supplies(SMPS)
- Uninterruptible Power Supply (UPS)

$V_{DS\ min@T_{jmax}}$	550	V
$R_{DS(ON)TYP.}$	460	m $\Omega$
$I_D$	7.2	A
$Q_g$	10	nC



Schematic diagram

◇ **Intrinsic fast-recovery body diode**

### Package Marking And Ordering Information

Device	Device Package	Marking
NCE50NF520F	TO-220F-3L	NCE50NF520F



TO-220F

**Table 1. Absolute Maximum Ratings ( $T_c=25^\circ\text{C}$ )**

Parameter	Symbol	Value	Unit
Drain-Source Voltage ( $V_{GS}=0V$ )	$V_{DS}$	500	V
Gate-Source Voltage ( $V_{DS}=0V$ ), AC ( $f>1\text{ Hz}$ )	$V_{GS}$	$\pm 30$	V
Gate-Source Voltage ( $V_{DS}=0V$ ), DC	$V_{GS}$	$\pm 20$	V
Continuous Drain Current at $T_c=25^\circ\text{C}$	$I_{D(DC)}$	7.2	A
Continuous Drain Current at $T_c=100^\circ\text{C}$	$I_{D(DC)}$	5.04	A
Pulsed drain current (Note 1)	$I_{DM(pulse)}$	21.6	A
Maximum Power Dissipation( $T_c=25^\circ\text{C}$ )	$P_D$	31.4	W
Derate above $25^\circ\text{C}$		0.21	W/ $^\circ\text{C}$
Single pulse avalanche current (Note 2)	$I_{AS}$	2.5	A
Reverse diode $dv/dt$ , $V_{DS} \leq 480\text{ V}$ , $I_{SD}<I_D$	$dv/dt$	15	V/ns
Drain Source voltage slope, $V_{DS} \leq 480\text{ V}$	$dv/dt$	50	V/ns
Operating Junction and Storage Temperature Range	$T_J, T_{STG}$	-55...+175	$^\circ\text{C}$

**Table 2. Thermal Characteristic**

Parameter	Symbol	Value	Unit
Thermal Resistance, Junction-to-Case (Maximum)	$R_{thJC}$	4.77	$^{\circ}\text{C}/\text{W}$
Thermal Resistance, Junction-to-Ambient (Maximum)	$R_{thJA}$	62	$^{\circ}\text{C}/\text{W}$

**Table 3. Electrical Characteristics (TA=25°C unless otherwise noted)**

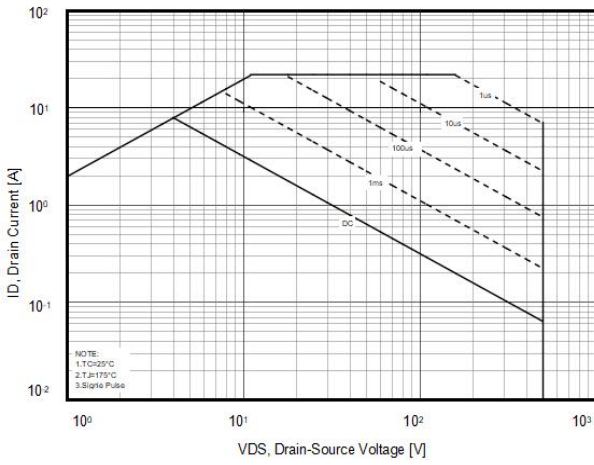
Parameter	Symbol	Condition	Min	Typ	Max	Unit
<b>On/off states</b>						
Drain-Source Breakdown Voltage	$BV_{DSS}$	$V_{GS}=0V, I_D=250\mu A$	500			V
Zero Gate Voltage Drain Current(Tc=25°C)	$I_{DSS}$	$V_{DS}=500V, V_{GS}=0V$			10	$\mu A$
Zero Gate Voltage Drain Current(Tc=125°C)	$I_{DSS}$	$V_{DS}=500V, V_{GS}=0V$			300	$\mu A$
Gate-Body Leakage Current	$I_{GSS}$	$V_{GS}=\pm 20V, V_{DS}=0V$			$\pm 200$	nA
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	3		5	V
Drain-Source On-State Resistance	$R_{DS(ON)}$	$V_{GS}=10V, I_D=3.5A$		460	520	m $\Omega$
<b>Dynamic Characteristics</b>						
Gate Resistance	$R_g$	F=1MHZ, D-S short		55		$\Omega$
Input Capacitance	$C_{iss}$	$V_{DS}=50V, V_{GS}=0V,$ F=1MHZ		354		pF
Output Capacitance	$C_{oss}$			20		pF
Reverse Transfer Capacitance	$C_{riss}$			4.7		pF
Total Gate Charge	$Q_g$	$V_{DS}=380V, I_D=3.5A,$ $V_{GS}=10V$		10		nC
Gate-Source Charge	$Q_{gs}$			4.5		nC
Gate-Drain Charge	$Q_{gd}$			2.6		nC
Gate plateau voltage	$V_{gp}$			7.2		V
<b>Switching times</b>						
Turn-on Delay Time	$t_{d(on)}$	$V_{DD}=380V, I_D=4A,$ $R_G=4\Omega, V_{GS}=10V$		8		nS
Turn-on Rise Time	$t_r$			10		nS
Turn-Off Delay Time	$t_{d(off)}$			41		nS
Turn-Off Fall Time	$t_f$			9		nS
<b>Source- Drain Diode Characteristics</b>						
Source-drain current(Body Diode)	$I_{SD}$	$T_c=25^{\circ}\text{C}$			7.2	A
Pulsed-Source-drain current(Body Diode)	$I_{SDM}$				21.6	A
Forward on voltage	$V_{SD}$	$T_j=25^{\circ}\text{C}, I_{SD}=7.2A, V_{GS}=0V$		1.0	1.2	V
Reverse Recovery Time	$t_{rr}$	$T_j=25^{\circ}\text{C}, I_F=4A,$ $di/dt=100A/\mu s$		105		nS
Reverse Recovery Charge	$Q_{rr}$			0.42		$\mu\text{C}$
Peak reverse recovery current	$I_{rrm}$			7.5		A

Notes: 1. Repetitive Rating: Pulse width limited by maximum junction temperature

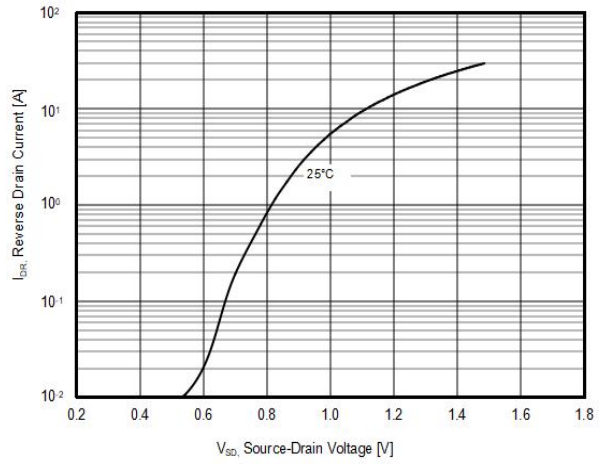
2.  $T_j=25^{\circ}\text{C}, V_{DD}=50V, V_G=10V, R_G=25\Omega$

## TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS (curves)

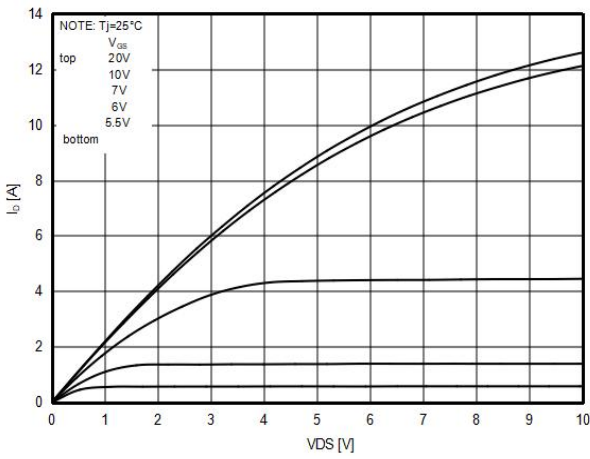
**Figure1. Safe operating area**



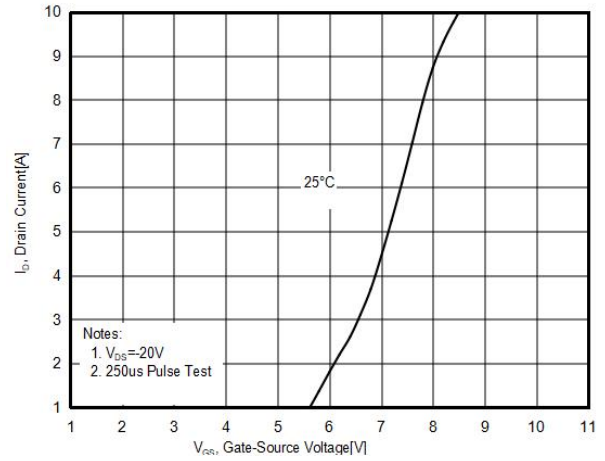
**Figure2. Source-Drain Diode Forward Voltage**



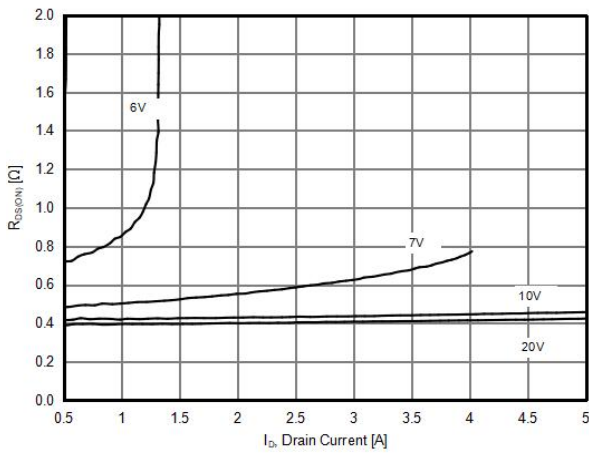
**Figure3. Output characteristics**



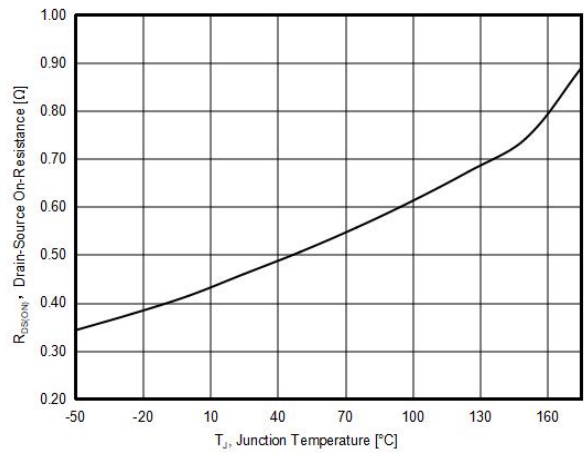
**Figure4. Transfer characteristics**



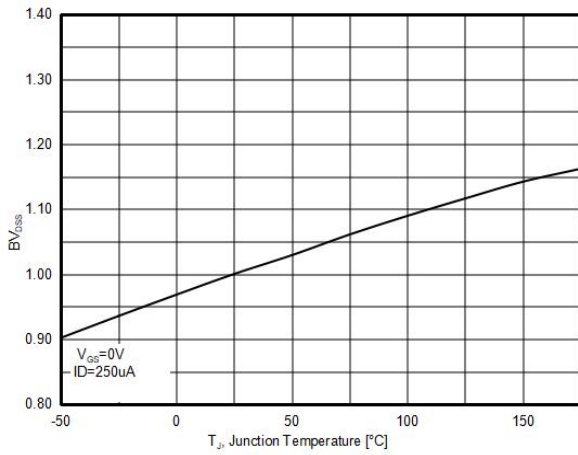
**Figure5. Static drain-source on resistance**



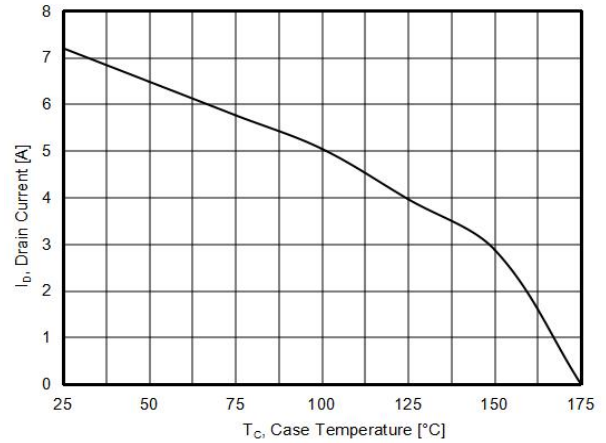
**Figure6.  $R_{DS(ON)}$  vs Junction Temperature**



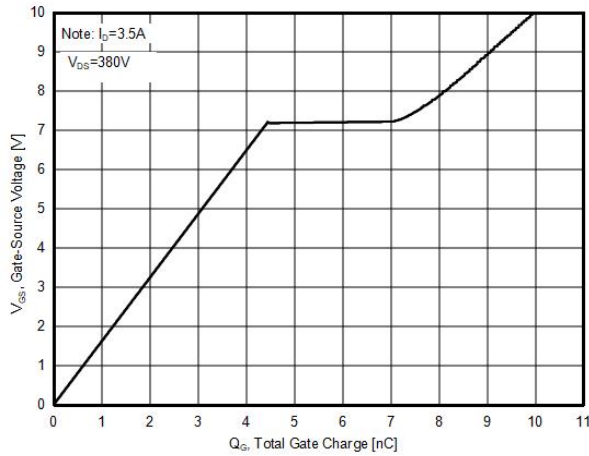
**Figure7.  $BV_{DSS}$  vs Junction Temperature**



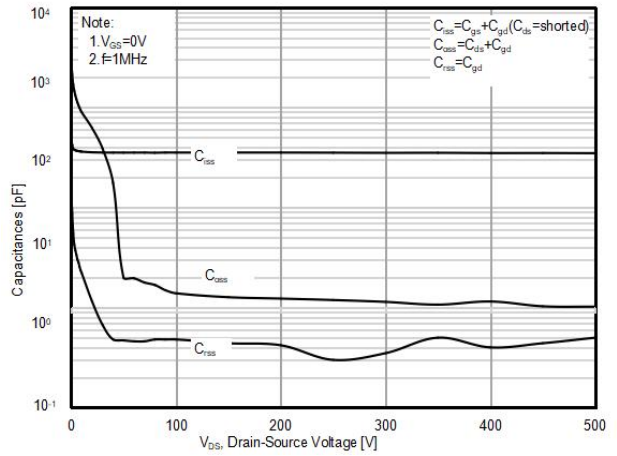
**Figure8. Maximum  $I_D$  vs Junction Temperature**



**Figure9. Gate charge waveforms**



**Figure10. Capacitance**

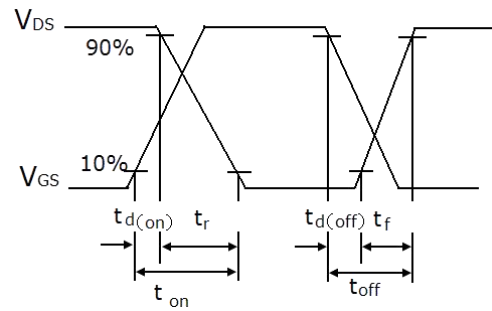


## Test circuit

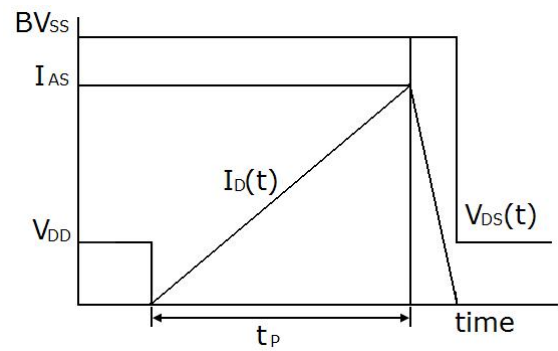
### 1) Gate charge test circuit & Waveform



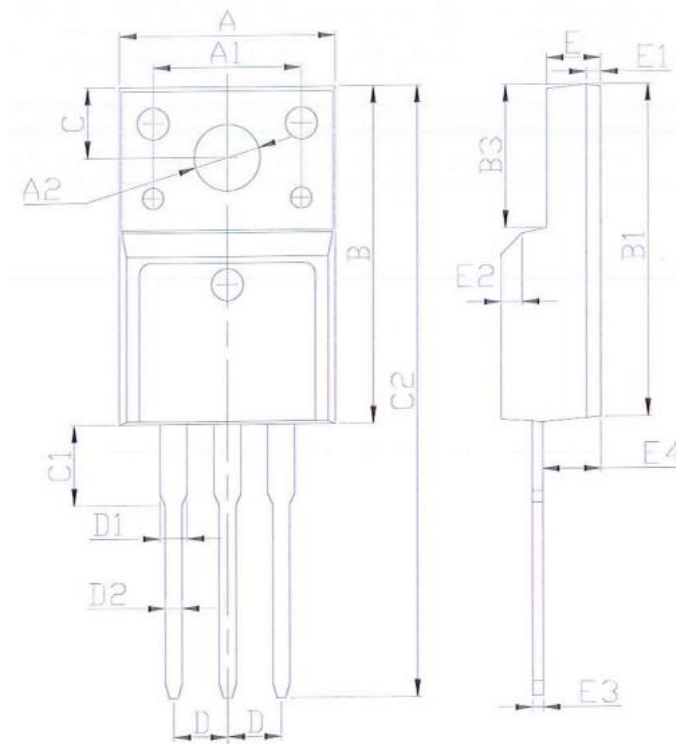
### 2) Switch Time Test Circuit:



### 3) Unclamped Inductive Switching Test Circuit & Waveforms

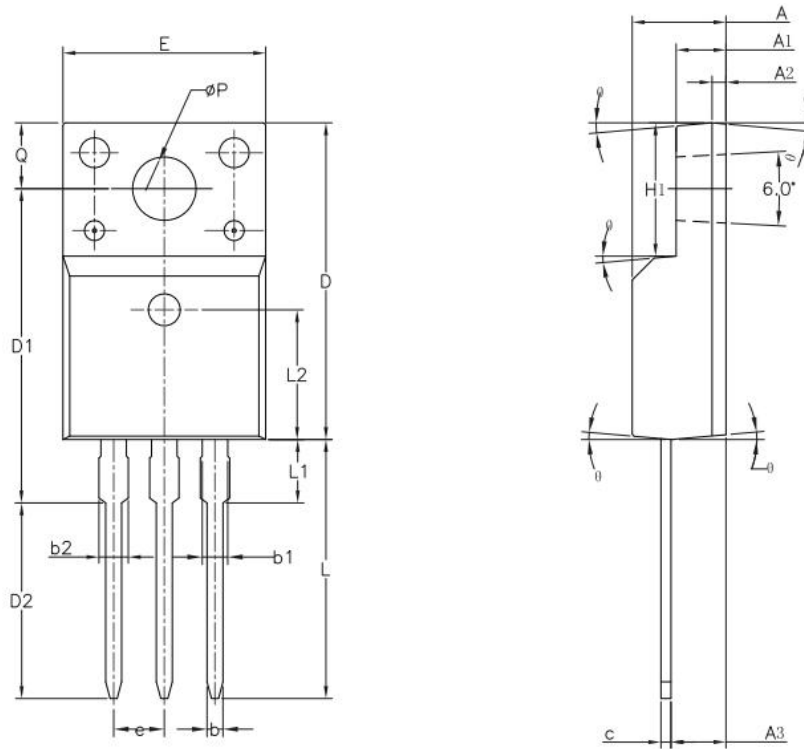


## TO-220F-3L-L Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	9.86	10.46	0.387	0.411
A1	6.80	7.20	0.267	0.283
A2	2.92	3.32	0.115	0.130
A3	9.40	10.00	0.369	0.393
B	15.40	16.40	0.605	0.644
B1	15.10	16.10	0.593	0.633
B2	4.40	5.00	0.173	0.196
B3	6.40	7.00	0.251	0.275
C	3.05	3.55	0.120	0.139
C1	2.95	3.55	0.116	0.139
C2	28.20	29.20	1.108	1.147
D	2.54 BSC		0.100 BSC	
D1	--	1.47	--	0.058
D2	0.60	1.00	0.024	0.039
E	2.30	2.80	0.090	0.110
E1	0.45	0.95	0.018	0.037
E2	45.0°		45.0°	
E3	0.30	0.70	0.012	0.028
E4	2.45	3.05	0.096	0.120

# TO-220F-3L-P Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	4.50	4.83	0.177	0.190
A1	2.34	2.74	0.092	0.108
A2	0.70 REF		0.028 REF	
A3	2.56	2.93	0.101	0.115
b	0.70	0.90	0.028	0.035
b1	1.18	1.38	0.046	0.054
b2	--	1.47	--	0.058
c	0.45	0.60	0.018	0.024
D	15.67	16.07	0.616	0.631
D1	15.55	15.95	0.611	0.627
D2	9.60	10.00	0.377	0.393
E	9.96	10.36	0.391	0.407
e	2.54 BSC		0.100 BSC	
H1	6.48	6.88	0.255	0.270
L	12.68	13.28	0.498	0.522
L1	--	3.50	--	0.138
L2	6.50 REF		0.255 REF	
ø P	3.08	3.28	0.121	0.129
Q	3.20	3.40	0.126	0.134

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